TMUX611x ±17V 低电容、低泄漏电流、精密四通道 SPST 开关

1 特性

- 宽电源电压范围：±5V 至 ±17V（双电源），10V 至 17V（但电源）
- 所有引脚的闩锁性都能达到 100mA，符合 JESD78 II 类 A 级要求
- 低导通电容：4.2pF
- 低输入泄漏：0.5pA
- 低电荷注入：0.6pC
- 轨至轨运行
- 低导通电阻：120Ω
- 快速开关开启时间：66ns
- 先断后合开关 (TMUX6113)
- EN 引脚可连接至 V_{DD}
- 低电源电流：17µA
- 人体放电模型 (HBM) ESD 保护：针对所有引脚提供 ±2kV 保护
- 行业标准 TSSOP 封装和较小的 WQFN 封装

2 应用

- 工厂自动化和工业过程控制
- 可编程逻辑控制器 (PLC)
- 模拟输入模块
- 半导体测试设备
- 电池测试设备

3 说明

TMUX6111、TMUX6112 和 TMUX6113 器件是现代化的互补金属氧化物半导体 (CMOS) 器件，具有四个独立的可选单刀单掷 (SPST) 开关。这些器件在双电源（±5V 至 ±17V）、单电源（10V 至 17V）或非对称电源供电时均能正常运行。所有数字输入均具有兼容晶体管-晶体管逻辑 (TTL) 的阈值，从而确保 TTL/CMOS 逻辑兼容性。

逻辑 0 会打开 TMUX6111 中数字控制输入上的开关。要打开 TMUX6112 中的开关，则需要逻辑 1。TMUX6113 有两个开关的数字控制逻辑与 TMUX6111 类似，而另外两个开关上的逻辑则与之相反。TMUX6113 具有先断后合开关，因此可用于交叉点开关应用。

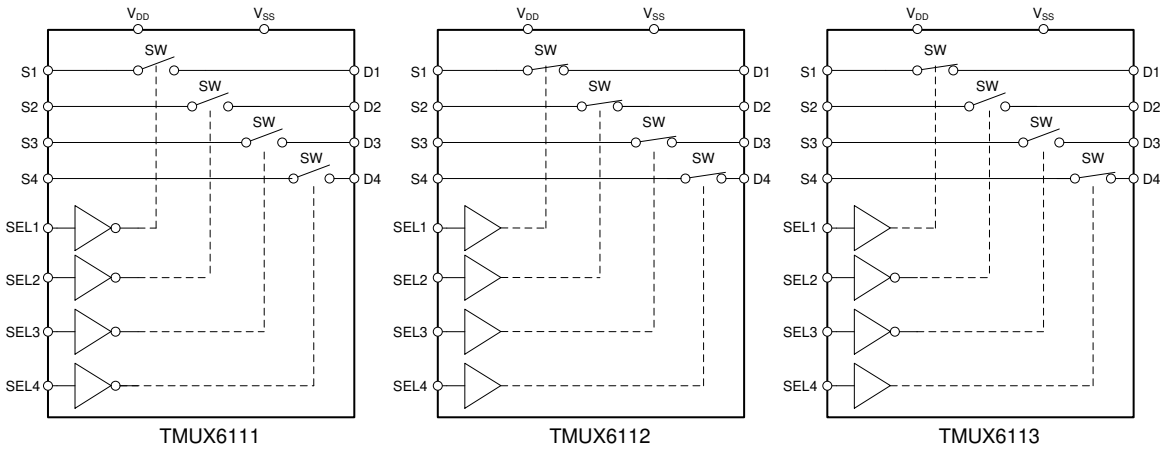
TMUX611x 器件是德州仪器 (TI) 精密开关和多路复用器系列的一部分。这些器件具有非常低的泄漏电流和电荷注入，因此可用于高精度测量 应用中的数字输入 D 类音频放大器。这些器件的电源电流低至 17µA，因此可用于便携式 应用供电的出色器件。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
TMUX6111 TMUX6112 TMUX6113	TSSOP (16)	5.00mm × 4.40mm
	WQFN (16)	3.00mm x 3.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

简化原理图



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4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision D (January 2019) to Revision E — **Page**

- 将*标题* 中的“TMUX611x ±16.5V”更改成了“TMUX611x ±17V” ... 1
- 将*特性* 中的“宽电源电压范围：±5V 至 ±16.5V（双电源），10V 至 16.5V（单电源）”更改成了“宽电源电压范围：±5V 至 ±17V（双电源），10V 至 17V（单电源）” ... 1
- 将*说明* 中的“双电源（±5V 至 ±16.5V）、单电源（10V 至 16.5V）”更改成了“双电源（±5V 至 ±17V）、单电源（10V 至 17V）” ... 1
- Changed ±16.5-V to ±17.5-V in the Description of the *Device Comparison Table* ... 4
- Changed recommended power supply voltage differential from 33 V to 34 V ... 5
- Changed recommended single supply voltage from 16.5 V to 17 V ... 5
- Changed positive and negative power supply voltage to +17 V and -17V ... 5
- The *Overview* From: dual supplies (±5 V to ±16.5 V) or single supply (10 V to 16.5 V) To: dual supplies (±5 V to ±17 V) or single supply (10 V to 17 V) ... 13
- Changed the *Application Information* From: 16.5 V (single supply) To: 17 V (single supply) ... 20
- The *Power Supply Recommendations* From: wide supply range of of ±5 V to ±16.5 V (10 V to 16.5 V in single-supply mode) To: wide supply range of of ±5 V to ±17 V (10 V to 17 V in single-supply mode) ... 22

Changes from Revision C (December 2018) to Revision D — **Page**

- Changed descriptions in the *Device Comparison Table* to match the data sheet title ... 4
- 已更改 图 30 to correct Op-Amp terminal polarities. ... 20

Changes from Revision B (November 2018) to Revision C — **Page**

- Changed units for channel current and ambient temperature. ... 6

Changes from Revision A (November 2018) to Revision B **Page**

- 针对 TMUX6111 和 TMUX6113 将文档状态从*产品预览* 更改成了*生产数据*..... 1

Changes from Original (August 2018) to Revision A **Page**

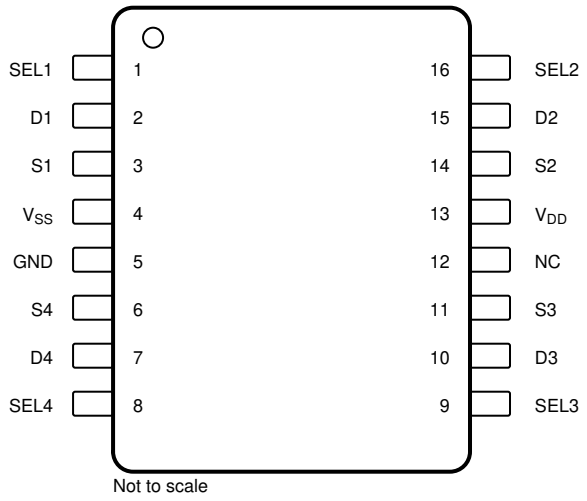
- 针对 TMUX6112 将文档状态从*预告信息* 更改成了*生产数据* 1

5 Device Comparison Table

PRODUCT	DESCRIPTION
TMUX6111	±17-V, Low-Capacitance, Low-Leakage-Current, Precision, Quad SPST Switches (Normally Closed)
TMUX6112	±17-V, Low-Capacitance, Low-Leakage-Current, Precision, Quad SPST Switches (Normally Open)
TMUX6113	±17-V, Low-Capacitance, Low-Leakage-Current, Precision, Quad SPST Switches (Dual Open + Dual Closed)

6 Pin Configuration and Functions

PW Package
16-Pin TSSOP
Top View



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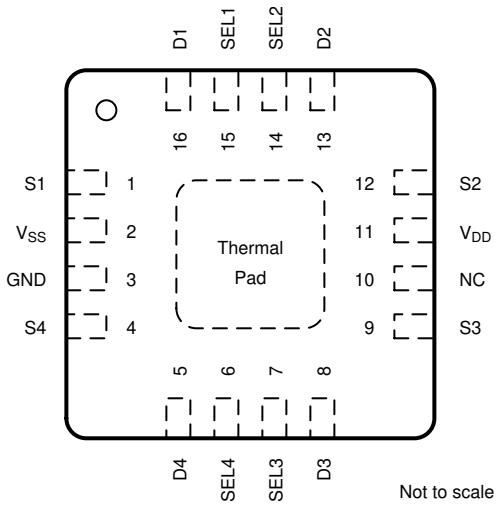
RTE Package
16-Pin WQFN
Top View



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Pin Functions

PIN			TYPE(1)	DESCRIPTION
NAME	TSSOP	WQFN		
SEL1	1	15	I	Logic control input 1.
D1	2	16	I/O	Drain pin 1. Can be an input or output.
S1	3	1	I/O	Source pin 1. Can be an input or output.
V_{SS}	4	2	P	Negative power supply. This pin is the most negative power-supply potential. In single-supply applications, this pin can be connected to ground. For reliable operation, connect a decoupling capacitor ranging from 0.1 µF to 10 µF between V_{SS} and GND.
GND	5	3	P	Ground (0 V) reference
S4	6	4	I/O	Source pin 4. Can be an input or output.
D4	7	5	I/O	Drain pin 4. Can be an input or output.
SEL4	8	6	I	Logic control input 4.
SEL3	9	7	I	Logic control input 3.
D3	10	8	I/O	Drain pin 3. Can be an input or output.
S3	11	9	I/O	Source pin 3. Can be an input or output.
NC	12	10	–	No internal connection.
V_{DD}	13	11	P	Positive power supply. This pin is the most positive power-supply potential. For reliable operation, connect a decoupling capacitor ranging from 0.1 µF to 10 µF between V_{DD} and GND.
S2	14	12	I/O	Source pin 2. Can be an input or output.
D2	15	13	I/O	Drain pin 2. Can be an input or output.
SEL2	16	14	I	Logic control input 2.
–	-	EP	–	Exposed Pad. The exposed pad is electrically connected to V_{SS} internally. Connect EP to V_{SS} to achieve rated thermal and ESD performance.

(1) I = input, O = output, I/O = input and output, P = power

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
V_{DD} to V_{SS}	Supply voltage		36	V
V_{DD} to GND		–0.3	18	V
V_{SS} to GND		–18	0.3	V
V_{DIG}	Digital input pin (SEL1, SEL2, SEL3, SEL4) voltage	GND –0.3	V_{DD}+0.3	V
I_{DIG}	Digital input pin (SEL1, SEL2, SEL3, SEL4) current	–30	30	mA
V_{ANA_IN}	Analog input pin (Sx) voltage	V_{SS}–0.3	V_{DD}+0.3	V
I_{ANA_IN}	Analog input pin (Sx) current	–30	30	mA
V_{ANA_OUT}	Analog output pin (D) voltage	V_{SS}–0.3	V_{DD}+0.3	V
I_{ANA_OUT}	Analog output pin (D) current	–30	30	mA
T_A	Ambient temperature	–55	140	°C
T_J	Junction temperature		150	°C
T_{stg}	Storage temperature	–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins(2)	±500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Thermal Information

THERMAL METRIC		TMUX6111/ TMUX6112/ TMUX6113		UNIT
		PW (TSSOP)	RTE (QFN)	
		16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	111.0	51.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	41.7	53.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	57.2	26.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	4.1	1.7	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	56.6	26.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	11.6	°C/W

7.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{DD} to V_{SS}(1)	Power supply voltage differential	10		34	V
V_{DD} to GND	Positive power supply voltage (singlle supply, V_{SS} = 0 V)	10		17	V
V_{DD} to GND	Positive power supply voltage (dual supply)	5		17	V
V_{SS} to GND	Negative power supply voltage (dual supply)	–5		–17	V
V_S(2)	Source pins voltage	V_{SS}		V_{DD}	V

(1) V_{DD} and V_{SS} can be any value as long as 10 V ≤ (V_{DD} – V_{SS}) ≤ 34 V.
(2) V_S is the voltage on all the S pins.

Recommended Operating Conditions (continued)

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_D	Drain pin voltage	V_{SS}		V_{DD}	V
V_{DIG}	Digital input pin (SEL1, SEL2, SEL3, SEL4) voltage	0		V_{DD}	V
I_{CH}	Channel current (T_A = 25°C)	–25		25	mA
T_A	Ambient temperature	–40		125	°C

7.5 Electrical Characteristics (Dual Supplies: ±15 V)

at T_A = 25°C, V_{DD} = 15 V, and V_{SS} = -15 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
ANALOG SWITCH							
V_A	Analog signal range		T_A = –40°C to +125°C	V_{SS}		V_{DD}	V
R_{ON}	On-resistance	V_S = 0 V, I_S = 1 mA			120	135	Ω
		V_S = ±10 V, I_S = 1 mA			140	160	Ω
			T_A = –40°C to +85°C			210	Ω
			T_A = –40°C to +125°C			245	Ω
ΔR_{ON}	On-resistance mismatch between channels	V_S = ±10 V, I_S = 1 mA			2.5	6	Ω
			T_A = –40°C to +85°C			9	Ω
			T_A = –40°C to +125°C			11	Ω
R_{ON_FLAT}	On-resistance flatness	V_S = –10 V, 0 V, +10 V, I_S = 1 mA			23	33	Ω
			T_A = –40°C to +85°C			37	Ω
			T_A = –40°C to +125°C			38	Ω
R_{ON_DRIFT}	On-resistance drift	V_S = 0 V			0.52		%/°C
$I_{S(OFF)}$	Source off leakage current(1)	Switch state is off, V_S = +10 V/ –10 V, V_D = –10 V/ + 10 V		–0.02	0.005	0.02	nA
			T_A = –40°C to +85°C	-0.14		0.05	nA
			T_A = –40°C to +125°C	–1.3		0.25	nA
$I_{D(OFF)}$	Drain off leakage current(1)	Switch state is off, V_S = +10 V/ –10 V, V_D = –10 V/ +10 V		–0.02	0.005	0.02	nA
			T_A = –40°C to +85°C	–0.14		0.05	nA
			T_A = –40°C to +125°C	–1.3		0.25	nA
$I_{D(ON)}$	Drain on leakage current	Switch state is on, V_S = +10 V/ –10 V, V_D = –10 V/ +10 V		–0.04	0.01	0.04	nA
			T_A = –40°C to +85°C	–0.25		0.1	nA
			T_A = –40°C to +125°C	–1.8		0.5	nA
DIGITAL INPUT (SELx pins)							
V_{IH}	Logic voltage high			2			V
V_{IL}	Logic voltage low					0.8	V
$R_{PD(IN)}$	Pull-down resistance on SELx pins				6		MΩ
POWER SUPPLY							
I_{DD}	V_{DD} supply current	V_A = 0 V or 3.3 V, V_S = 0 V			17	21	µA
			T_A = –40°C to +85°C			22	µA
			T_A = –40°C to +125°C			23	µA
I_{SS}	V_{SS} supply current	V_A = 0 V or 3.3 V, V_S = 0 V			8	10	µA
			T_A = –40°C to +85°C			11	µA
			T_A = –40°C to +125°C			12	µA

(1) When V_S is positive, V_D is negative, and vice versa.

7.6 Switching Characteristics (Dual Supplies: ±15 V)

at T_A = 25°C, V_{DD} = 15 V, and V_{SS} = -15 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{ON}	Enable turn-on time	V_S = ±10 V, R_L = 300 Ω , C_L = 35 pF		66	78	ns
		V_S = ±10 V, R_L = 300 Ω , C_L = 35 pF, T_A = –40°C to +85°C			107	ns
		V_S = ±10 V, R_L = 300 Ω , C_L = 35 pF, T_A = –40°C to +125°C			117	ns
t_{OFF}	Enable turn-off time	V_S = ±10 V, R_L = 300 Ω , C_L = 35 pF		56	68	ns
		V_S = ±10 V, R_L = 300 Ω , C_L = 35 pF, T_A = –40°C to +85°C			77	ns
		V_S = ±10 V, R_L = 300 Ω , C_L = 35 pF, T_A = –40°C to +125°C			81	ns
tBBM	Break-before-make time delay (TMUX6113 Only)	V_S = 10 V, R_L = 300 Ω , C_L = 35 pF, T_A = –40°C to +125°C	8	40		ns
Q_J	Charge injection	V_S = 0 V, R_S = 0 Ω , C_L = 1 nF		0.6		pC
O_{ISO}	Off-isolation	R_L = 50 Ω , C_L = 5 pF, f = 1 MHz		–85		dB
X_{TALK}	Channel-to-channel crosstalk	R_L = 50 Ω , C_L = 5 pF, f = 1 MHz, adjacent channel		–100		dB
		R_L = 50 Ω , C_L = 5 pF, f = 1 MHz, non-adjacentchannel		–115		dB
I_L	Insertion loss	R_L = 50 Ω , C_L = 5 pF, f = 1 MHz		–7.0		dB
ACPSRR	AC Power Supply Rejection Ratio	R_L = 10 kΩ , C_L = 5 pF, V_{PP}= 0.62 V on V_{DD}, f= 1 MHz		–59		dB
		R_L = 10 kΩ , C_L = 5 pF, V_{PP}= 0.62 V on V_{SS}, f= 1 MHz		–59		dB
BW	-3dB Bandwidth	R_L = 50 Ω , C_L = 5 pF		800		MHz
THD	Total harmonic distortion + noise	R_L = 10k Ω , C_L = 5 pF, f= 20Hz to 20kHz		0.08		%
C_{IN}	Digital input capacitance	V_{IN} = 0 V or V_{DD}		1.5		pF
$C_{S(OFF)}$	Source off-capacitance	V_S = 0 V, f = 1 MHz (PW package)		1.9	3.0	pF
		V_S = 0 V, f = 1 MHz (RTE package)		2.5	3.6	pF
$C_{D(OFF)}$	Drain off-capacitance	V_S = 0 V, f = 1 MHz		2.4	3.1	pF
$C_{S(ON)}$, $C_{D(ON)}$	Source and drain on-capacitance	V_S = 0 V, f = 1 MHz		4.2	6.0	pF

7.7 Electrical Characteristics (Single Supply: 12 V)

at T_A = 25°C, V_{DD} = 12 V, and V_{SS} = 0 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
ANALOG SWITCH							
V_A	Analog signal range	T_A = –40°C to +125°C		V_{SS}		V_{DD}	V
R_{ON}	On-resistance	V_S = 10 V, I_S = 1 mA			230	265	Ω
			T_A = –40°C to +85°C			355	Ω
			T_A = –40°C to +125°C			405	Ω
ΔR_{ON}	On-resistance mismatch between channels	V_S = 10 V, I_S = 1 mA			5	12	Ω
			T_A = –40°C to +85°C			19	Ω
			T_A = –40°C to +125°C			23	Ω
R_{ON_DRIFT}	On-resistance drift	V_S = 0 V			0.5		%/°C
$I_{S(OFF)}$	Source off leakage current(1)	Switch state is off, V_S = 10 V/ 1 V, V_D = 1 V/ 10 V		–0.02	0.005	0.02	nA
			T_A = –40°C to +85°C	–0.1		0.04	nA
			T_A = –40°C to +125°C	-1		0.2	nA

(1) When V_S is positive, V_D is negative, and vice versa.

Electrical Characteristics (Single Supply: 12 V) (continued)

at T_A = 25°C, V_{DD} = 12 V, and V_{SS} = 0 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
$I_{D(OFF)}$	Drain off leakage current(1)	Switch state is off, V_S = 10 V/ 1 V, V_D = 1 V/ 10 V		–0.02	0.005	0.02	nA
			T_A = –40°C to +85°C	–0.1		0.04	nA
			T_A = –40°C to +125°C	–1		0.2	nA
$I_{D(ON)}$	Drain on leakage current	Switch state is on, V_S = floating, V_D = 1 V/ 10 V		–0.04	0.01	0.04	nA
			T_A = –40°C to +85°C	–0.16		0.08	nA
			T_A = –40°C to +125°C	–1.4		0.4	nA
DIGITAL INPUT (SELx pins)							
V_{IH}	Logic voltage high			2			V
V_{IL}	Logic voltage low					0.8	V
$R_{PD(EN)}$	Pull-down resistance on SELx pins				6		MΩ
POWER SUPPLY							
I_{DD}	V_{DD} supply current	V_A = 0 V or 3.3 V, V_S = 0 V			13	16	µA
			T_A = –40°C to +85°C			17	µA
			T_A = –40°C to +125°C			18	µA

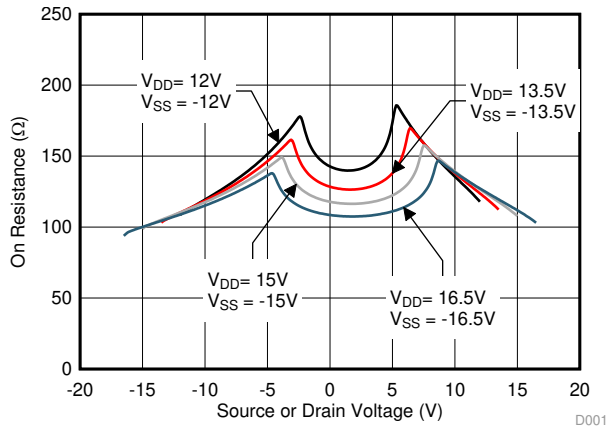
7.8 Switching Characteristics (Single Supply: 12 V)

at T_A = 25°C, V_{DD} = 12 V, and V_{SS} = 0 V (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{ON}	Enable turn-on time	V_S = 8 V, R_L = 300 Ω , C_L = 35 pF		72	84	ns
		V_S = 8 V, R_L = 300 Ω , C_L = 35 pF, T_A = –40°C to +85°C			117	ns
		V_S = 8 V, R_L = 300 Ω , C_L = 35 pF, T_A = –40°C to +125°C			128	ns
t_{OFF}	Enable turn-off time	V_S = 8 V, R_L = 300 Ω , C_L = 35 pF		57	66	ns
		V_S = 8 V, R_L = 300 Ω , C_L = 35 pF, T_A = –40°C to +85°C			78	ns
		V_S = 8 V, R_L = 300 Ω , C_L = 35 pF, T_A = –40°C to +125°C			84	ns
t_{BBM}	Break-before-make time delay (TMUX6113 only)	V_S = 8 V, R_L = 300 Ω , C_L = 35 pF, T_A = –40°C to +125°C	17	47		ns
Q_J	Charge injection	V_S = 0 V to 12 V, R_S = 0 Ω , C_L = 1 nF		0.6		pC
O_{ISO}	Off-isolation	R_L = 50 Ω , C_L = 5 pF, f = 1 MHz		–86		dB
X_{TALK}	Channel-to-channel crosstalk	R_L = 50 Ω , C_L = 5 pF, f = 1 MHz, adjacent channel		–98		dB
		R_L = 50 Ω , C_L = 5 pF, f = 1 MHz, non-adjacent channel		–117		dB
I_L	Insertion loss	R_L = 50 Ω , C_L = 5 pF, f = 1 MHz		-14		dB
ACPSRR	AC Power Supply Rejection Ratio	R_L = 10 kΩ , C_L = 5 pF, V_{PP}= 0.62 V, f= 1 MHz		–59		dB
BW	-3dB Bandwidth	R_L = 50 Ω , C_L = 5 pF		750		MHz
C_{IN}	Digital input capacitance	V_{IN} = 0 V or V_{DD}		1.6		pF
$C_{S(OFF)}$	Source off-capacitance	V_S = 6 V, f = 1 MHz (PW package)		2.2	3.1	pF
		V_S = 6 V, f = 1 MHz (RTE package)		2.9	4.0	pF
$C_{D(OFF)}$	Drain off-capacitance	V_S = 6 V, f = 1 MHz		2.8	3.5	pF
$C_{S(ON)}$, $C_{D(ON)}$	Source and drain on-capacitance	V_S = 6 V, f = 1 MHz		4.6	6.3	pF

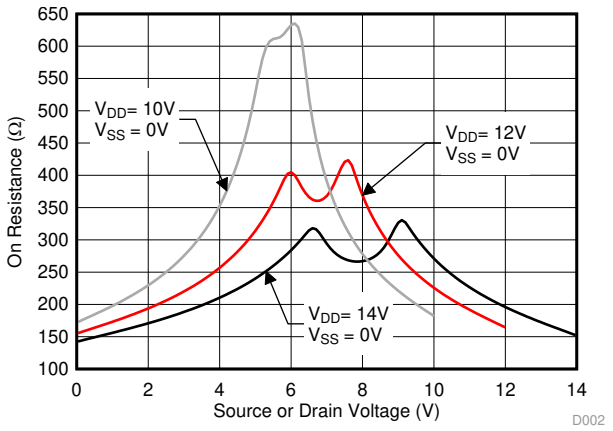
7.9 Typical Characteristics

at T_A = 25°C, V_{DD} = 15 V, and V_{SS} = –15 V (unless otherwise noted)



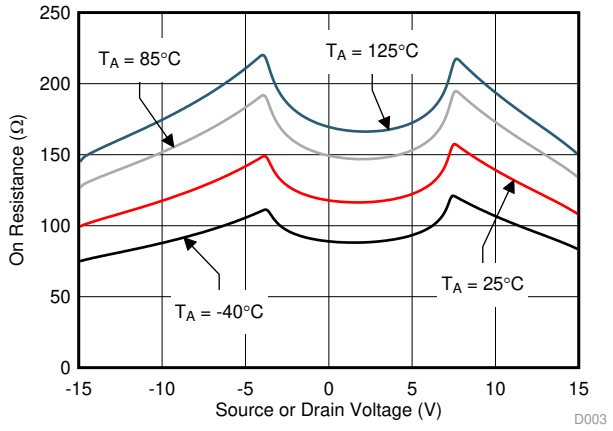
Dual Supply Operation (T_A = 25°C)

图 1. On-Resistance vs Source or Drain Voltage



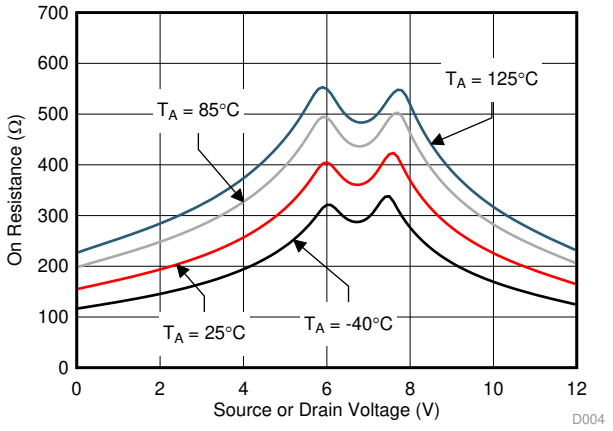
Single Supply Operation (T_A = 25°C)

图 2. On-Resistance vs Source or Drain Voltage



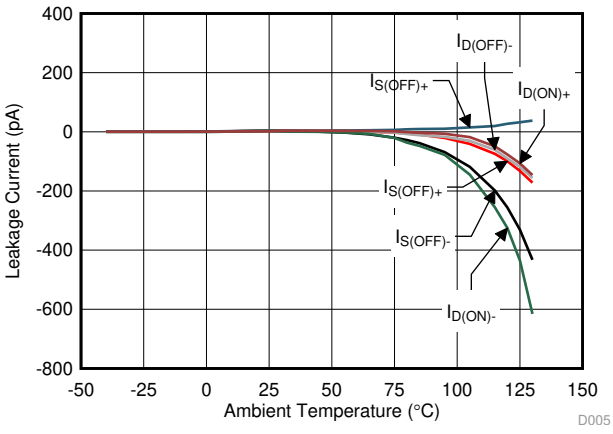
V_{DD} = 15 V, V_{SS} = –15 V

图 3. On-Resistance vs Source or Drain Voltage



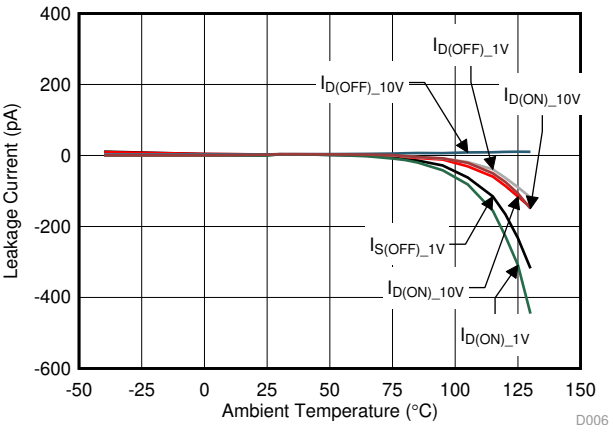
V_{DD} = 12 V, V_{SS} = 0 V

图 4. On-Resistance vs Source or Drain Voltage



V_{DD} = 15 V, V_{SS} = –15 V

图 5. Leakage Current vs Temperature

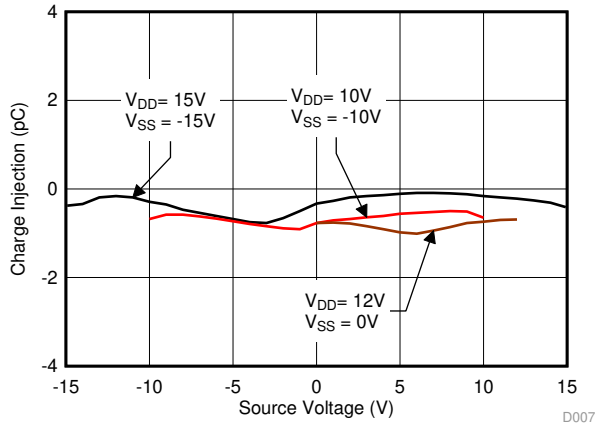


V_{DD} = 12 V, V_{SS} = 0 V

图 6. Leakage Current vs Temperature

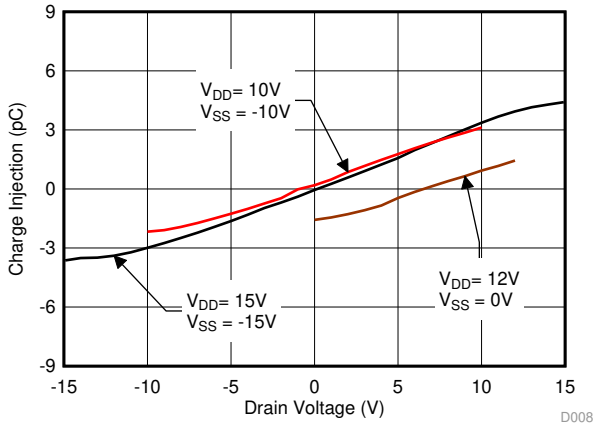
Typical Characteristics (接下页)

at T_A = 25°C, V_{DD} = 15 V, and V_{SS} = –15 V (unless otherwise noted)



T_A = 25°C

图 7. Charge Injection vs Source Voltage



T_A = 25°C

图 8. Charge Injection vs Drain Voltage

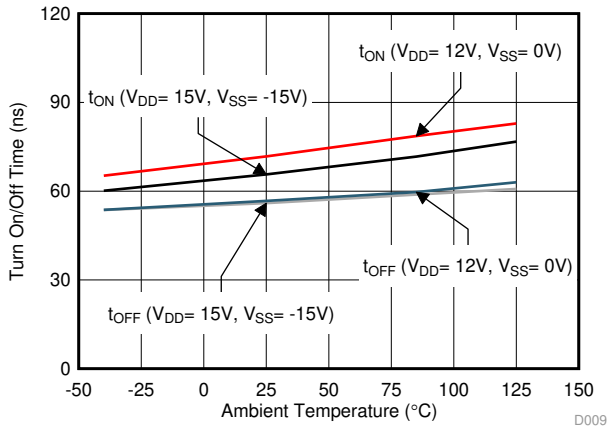
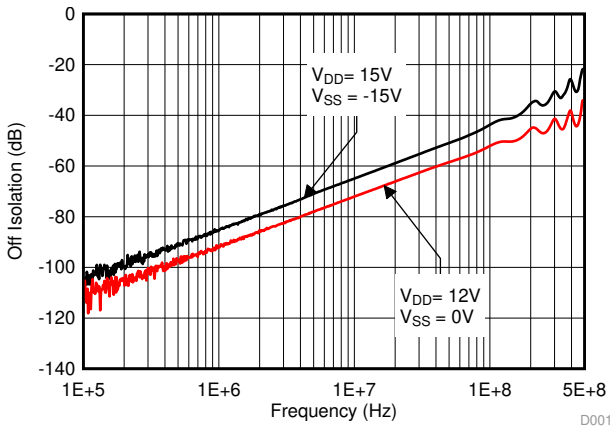
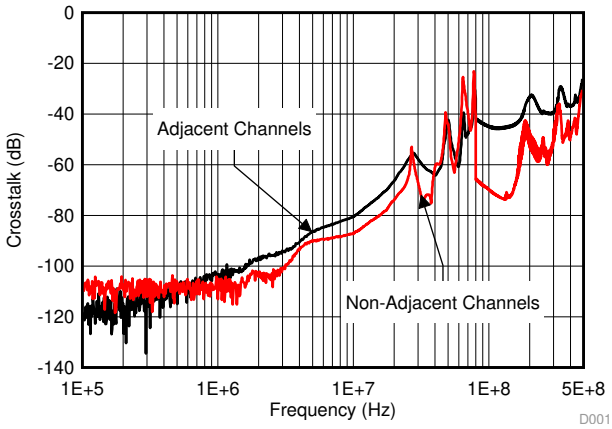


图 9. Turn-On and Turn-Off Times vs Temperature



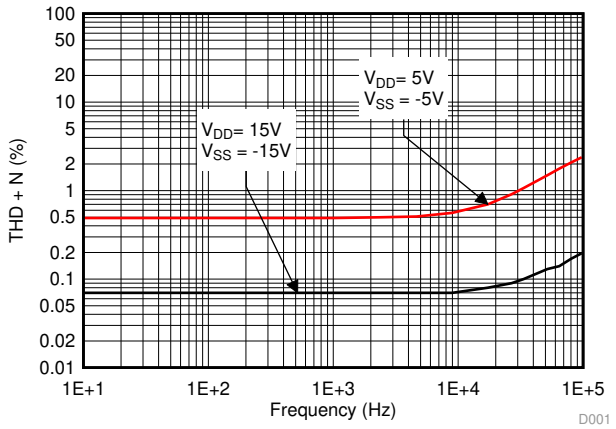
T_A = 25°C

图 10. Off Isolation vs Frequency



V_{DD} = 15 V, V_{SS} = –15 V, T_A = 25°C

图 11. Crosstalk vs Frequency

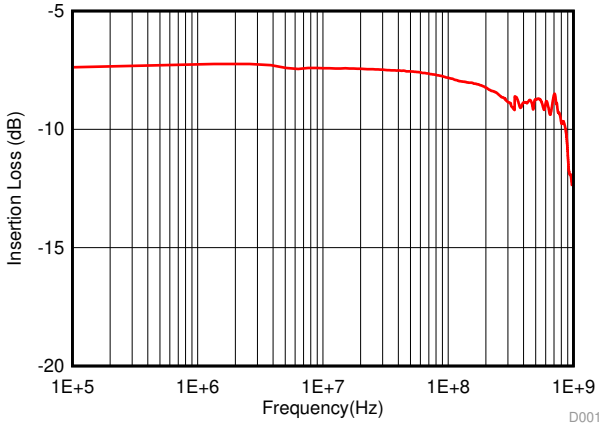


T_A = 25°C

图 12. THD+N vs Frequency

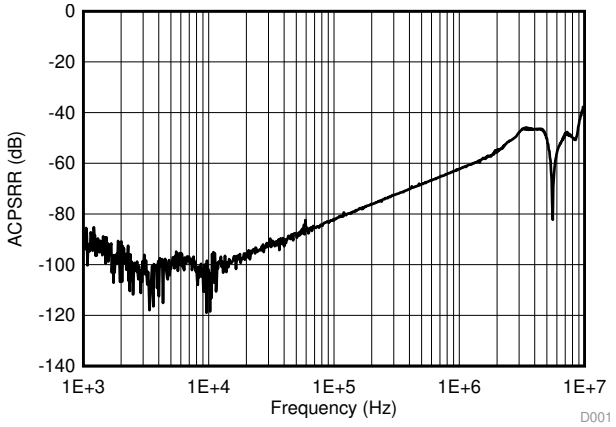
Typical Characteristics (接下页)

at T_A = 25°C, V_{DD} = 15 V, and V_{SS} = –15 V (unless otherwise noted)



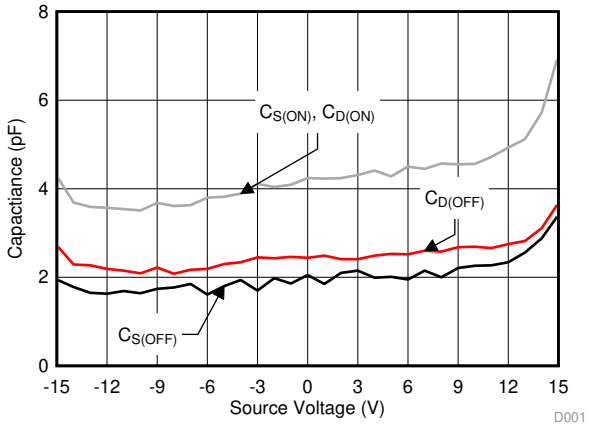
V_{DD} = 15 V, V_{SS} = –15 V, T_A = 25°C

图 13. On Response vs Frequency



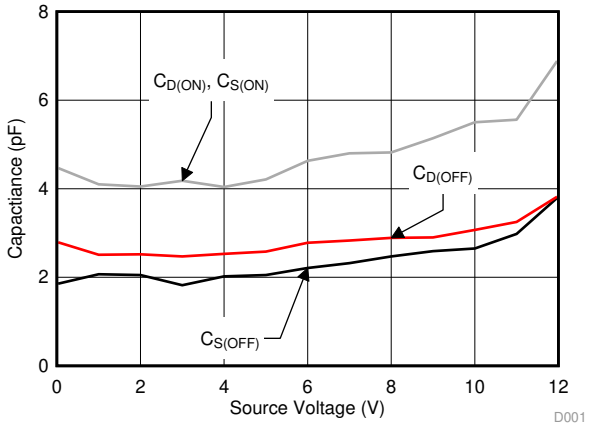
V_{DD} = 15 V, V_{SS} = –15 V, V_{PP}= 0.62 V, T_A = 25°C

图 14. ACPSRR vs Frequency



V_{DD} = 15 V, V_{SS} = –15 V, T_A = 25°C

图 15. Capacitance vs Source Voltage



V_{DD} = 12 V, V_{SS} = 0 V, T_A = 25°C

图 16. Capacitance vs Source Voltage

8 Parameter Measurement Information

8.1 Truth Tables

表 1, 表 2, 表 3and show the truth tables for the TMUX6111, TMUX6112, and TMUX6113, respectively.

表 1. TMUX6111 Truth Table

SELx	STATE
0	All Switch ON
1	All Switch OFF

表 2. TMUX6112 Truth Table

SELx	STATE
0	All Switch OFF
1	All Switch ON

表 3. TUMUX6113 Truth Table

SELx	STATE
0	Switch 1, 4 OFF Switch 2, 3 ON
1	Switch 1, 4 ON Switch 2, 3 OFF

9 Detailed Description

9.1 Overview

The TMUX6111, TMUX6112, and TMUX6113 are 4-channel single-pole/ single-throw (SPDT) switches that supports dual supplies (±5 V to ±17 V) or single supply (10 V to 17 V) operation. Each channel of the switch is turned on or turned off based on the state of its corresponding SELx pin. The Functional Block Diagram section provides a top-level block diagram of the switches.

9.1.1 On-Resistance

The on-resistance of the TMUX6111, TMUX6112, and TMUX6113 is the ohmic resistance across the source (Sx) and drain (Dx) pins of the device. The on-resistance varies with input voltage and supply voltage. The symbol R_{ON} is used to denote on-resistance. The measurement setup used to measure R_{ON} is shown in 图 17. Voltage (V) and current (I_{CH}) are measured using this setup, and R_{ON} is computed as shown in 公式 1:

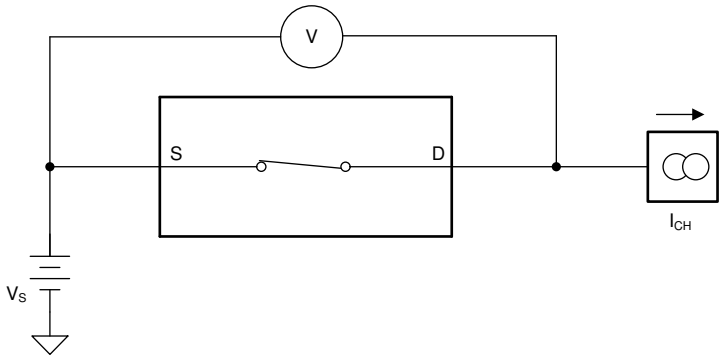


图 17. On-Resistance Measurement Setup

$$R_{ON} = V / I_{CH} \quad (1)$$

9.1.2 Off-Leakage Current

There are two types of leakage currents associated with a switch during the off state:

1. Source off-leakage current
2. Drain off-leakage current

Source leakage current is defined as the leakage current flowing into or out of the source pin when the switch is off. This current is denoted by the symbol $I_{S(OFF)}$.

Drain leakage current is defined as the leakage current flowing into or out of the drain pin when the switch is off. This current is denoted by the symbol $I_{D(OFF)}$.

The setup used to measure both off-leakage currents is shown in 图 18

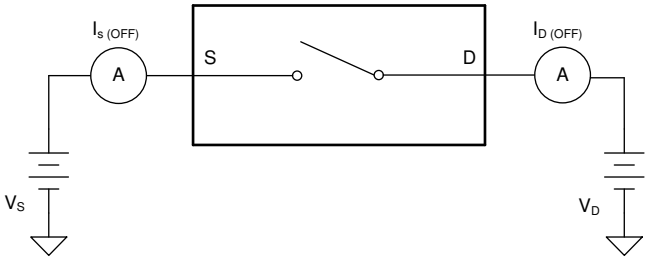


图 18. Off-Leakage Measurement Setup

Overview (接下页)

9.1.3 On-Leakage Current

On-leakage current is defined as the leakage current that flows into or out of the drain pin when the switch is in the on state. The source pin is left floating during the measurement. 图 19 shows the circuit used for measuring the on-leakage current, denoted by $I_{D(ON)}$.

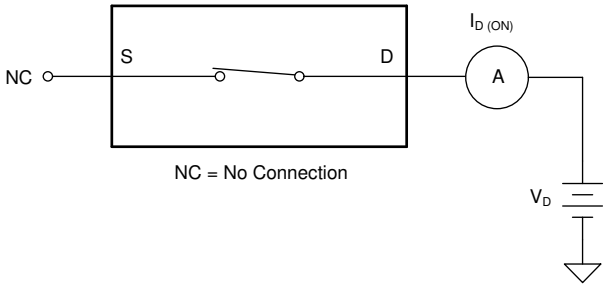


图 19. On-Leakage Measurement Setup

9.1.4 Break-Before-Make Delay

The break-before-make delay is a safety feature of the TMUX6113 switch. The TMUX6113's ON switches first break the connection before the OFF switches make connection. The time delay between the *break* and the *make* is known as break-before-make delay. 图 20 shows the setup used to measure break-before-make delay, denoted by the symbol t_{BBM}.

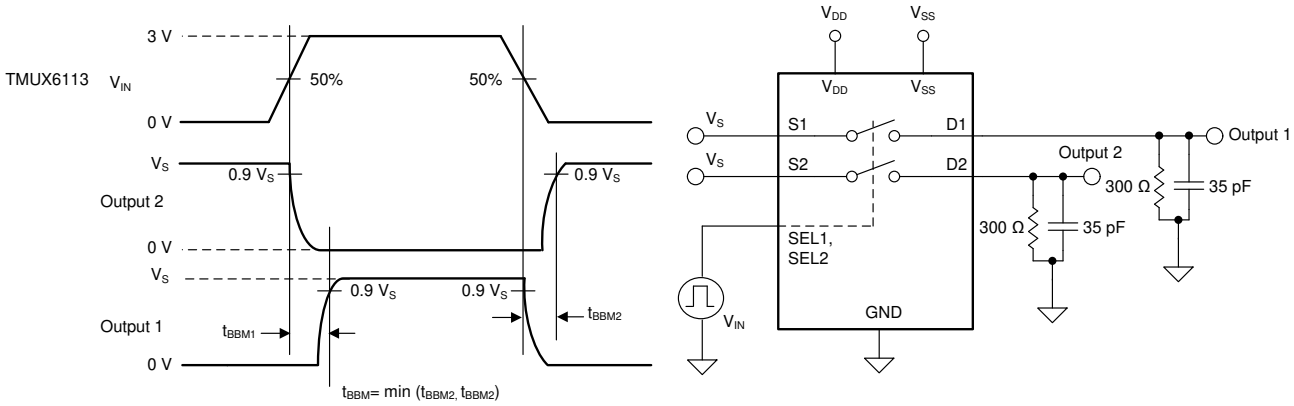


图 20. Break-Before-Make Delay Measurement Setup

9.1.5 Turn-On and Turn-Off Time

Turn-on time is defined as the time taken by the output of the TMUX6111, TMUX6112, and TMUX6113 to rise to a 90% final value after the SELx signal has risen (for NC switches) or fallen (for NO switches) to a 50% final value. 图 21 shows the setup used to measure turn-on time. Turn-on time is denoted by the symbol t_{ON}.

Turn off time is defined as the time taken by the output of the TMUX6111, TMUX6112, and TMUX6113 to fall to a 10% initial value after the SELx signal has fallen (for NC switches) or risen (for NO switches) to a 50% initial value. 图 21 shows the setup used to measure turn-off time. Turn-off time is denoted by the symbol t_{OFF}.

Overview (接下页)

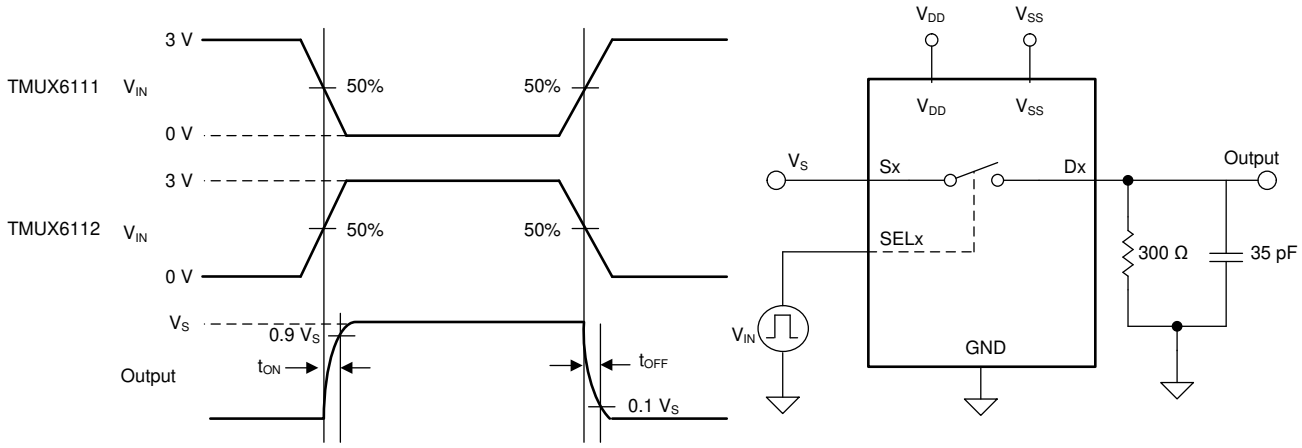


图 21. Turn-On and Turn-Off Time Measurement Setup

9.1.6 Charge Injection

The TMUX6111, TMUX6112, and TMUX6113 have a simple transmission-gate topology. Any mismatch in capacitance between the NMOS and PMOS transistors results in a charge injected into the drain or source during the falling or rising edge of the gate signal. The amount of charge injected into the source or drain of the device is known as charge injection, and is denoted by the symbol Q_{INJ}. 图 22 shows the setup used to measure charge injection.

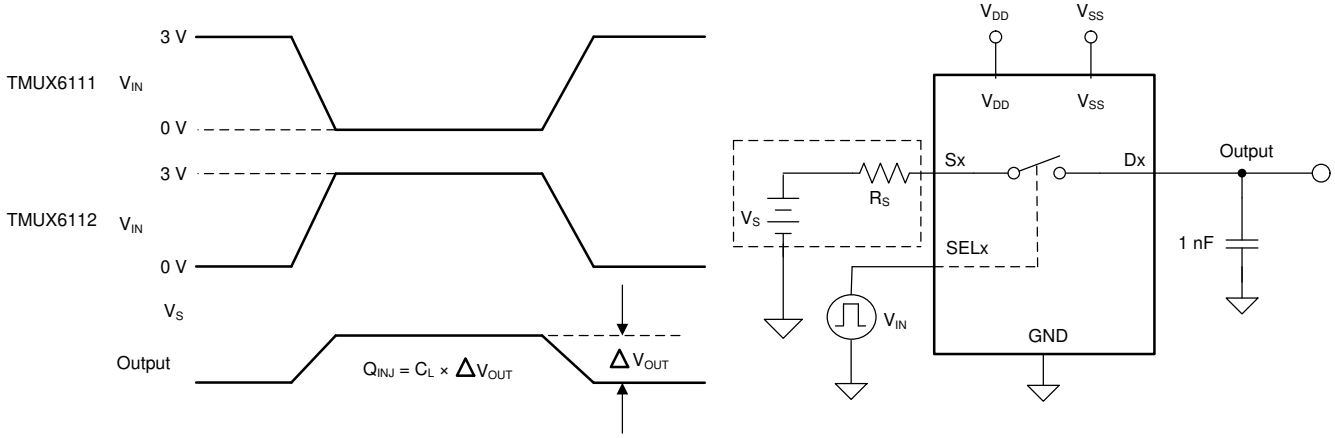


图 22. Charge-Injection Measurement Setup

9.1.7 Off Isolation

Off isolation is defined as the voltage at the drain pin (Dx) of the TMUX6111, TMUX6112, and TMUX6113 when a 1-V_{RMS} signal is applied to the source pin (Sx) of an OFF switch. 图 23 shows the setup used to measure off isolation. Use 公式 2 to compute off isolation.

Overview (接下页)

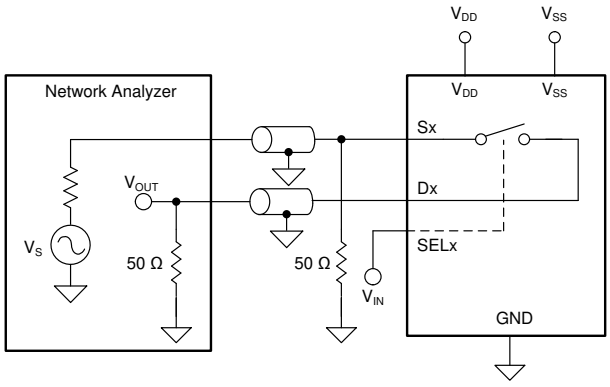


图 23. Off Isolation Measurement Setup

$$\text{Off Isolation} = 20 \cdot \text{Log}\left(\frac{V_{OUT}}{V_S}\right) \quad (2)$$

9.1.8 Channel-to-Channel Crosstalk

Channel-to-channel crosstalk is defined as the voltage at the source pin (Sx) of an off-channel, when a 1-V_{RMS} signal is applied at the source pin of an on-channel. 图 24 shows the setup used to measure, and 公式 3 is the equation used to compute, channel-to-channel crosstalk.

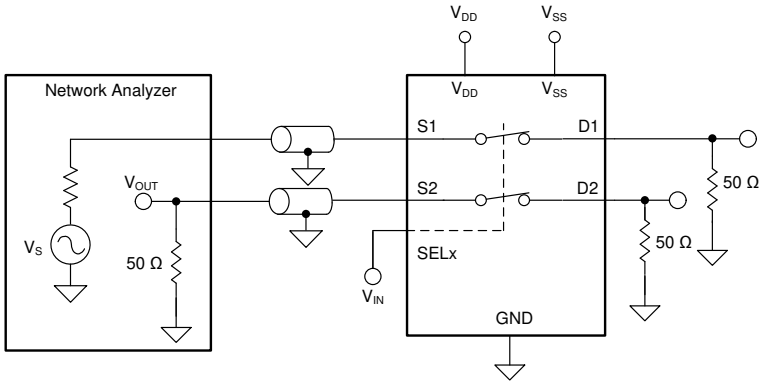


图 24. Channel-to-Channel Crosstalk Measurement Setup

$$\text{Channel-to-Channel Crosstalk} = 20 \cdot \text{Log}\left(\frac{V_{OUT}}{V_S}\right) \quad (3)$$

9.1.9 Bandwidth

Bandwidth is defined as the range of frequencies that are attenuated by < 3 dB when the input is applied to the source pin (Sx) of an on-channel, and the output is measured at the drain pin (Dx) of the TMUX6111, TMUX6112, and TMUX6113. 图 25 shows the setup used to measure bandwidth of the switch. Use 公式 4 to compute the attenuation.

Overview (接下页)

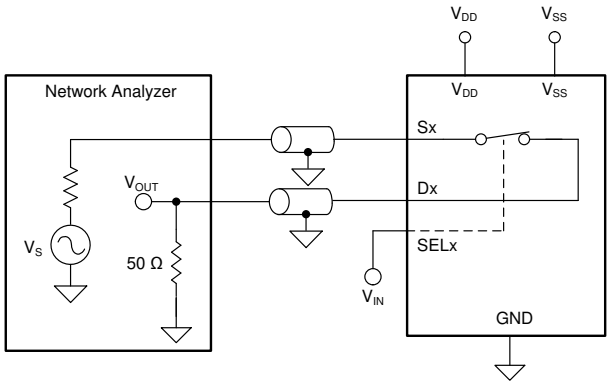


图 25. Bandwidth Measurement Setup

$$\text{Attenuation} = 20 \cdot \text{Log}\left(\frac{V_2}{V_1}\right) \tag{4}$$

9.1.10 THD + Noise

The total harmonic distortion (THD) of a signal is a measurement of the harmonic distortion, and is defined as the ratio of the sum of the powers of all harmonic components to the power of the fundamental frequency at the mux output. The on-resistance of the TMUX6111, TMUX6112, and TMUX6113 varies with the amplitude of the input signal and results in distortion when the drain pin is connected to a low-impedance load. Total harmonic distortion plus noise is denoted as THD+N. 图 26 shows the setup used to measure THD+N of the TMUX6111, TMUX6112, and TMUX6113.

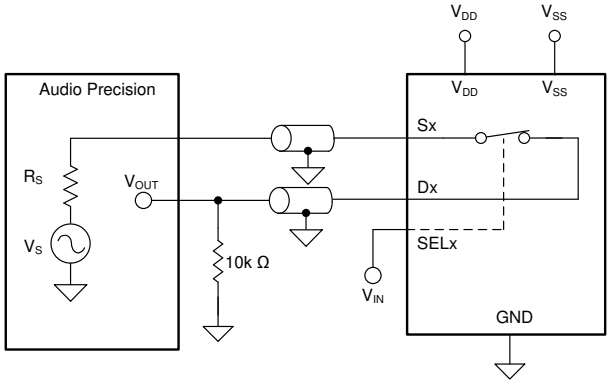
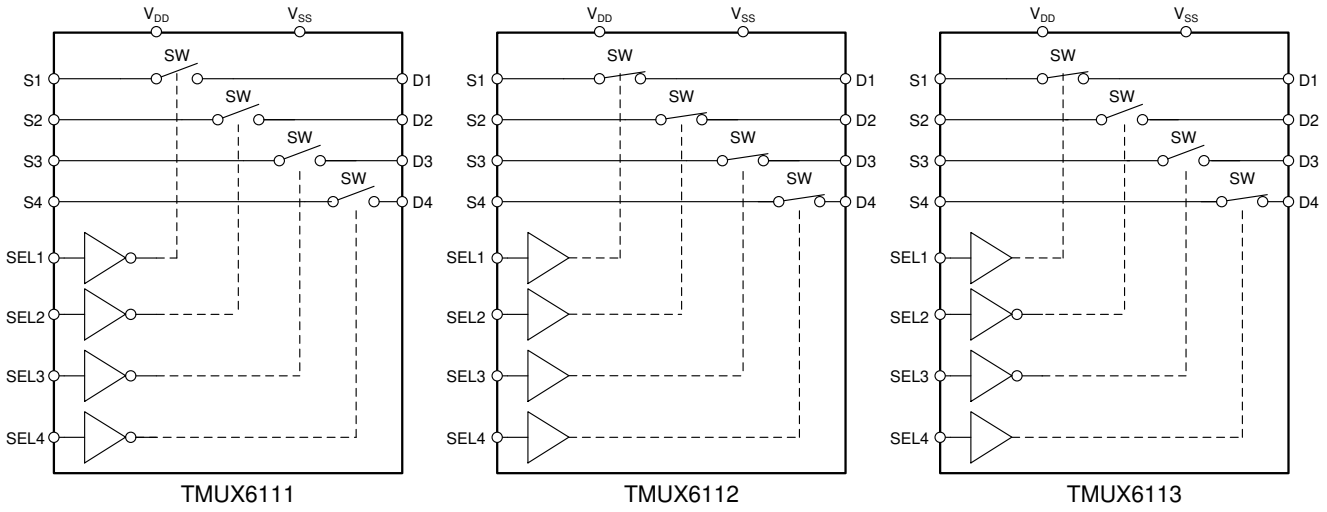


图 26. THD+N Measurement Setup

9.2 Functional Block Diagram



9.3 Feature Description

9.3.1 Ultra-low Leakage Current

The TMUX6111, TMUX6112, and TMUX6113 provide extremely low on- and off-leakage currents. The devices are capable of switching signals from high source-impedance inputs into a high input-impedance op amp with minimal offset error because of the ultralow leakage currents. 图 27 shows typical leakage currents of the devices versus temperature.

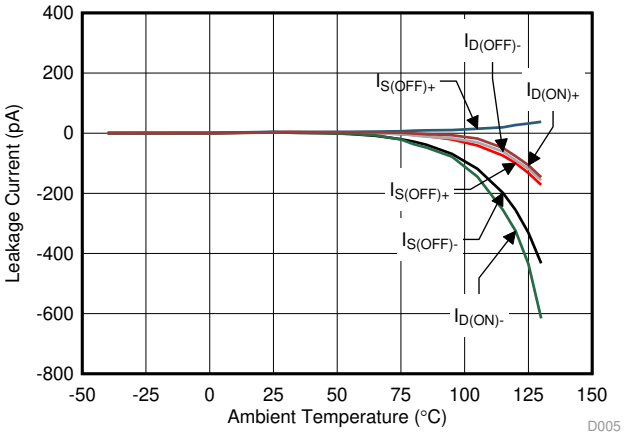


图 27. Leakage Current vs Temperature

9.3.2 Ultra-low Charge Injection

The TMUX6111, TMUX6112, and TMUX6113 are implemented with simple transmission gate topology, as shown in 图 28. Any mismatch in the stray capacitance associated with the NMOS and PMOS causes an output level change whenever the switch is opened or closed. The devices utilize special charge-injection cancellation circuitry that reduces the source (Sx)-to-drain (Dx) charge injection to as low as 0.6 pC at V_S = 0 V, as shown in 图 29.

Feature Description (接下页)

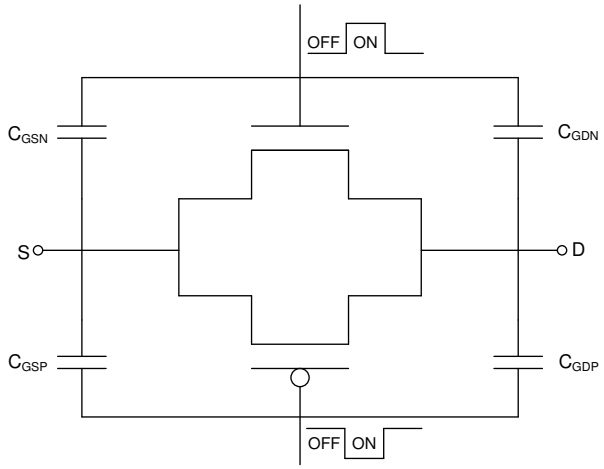


图 28. Transmission Gate Topology

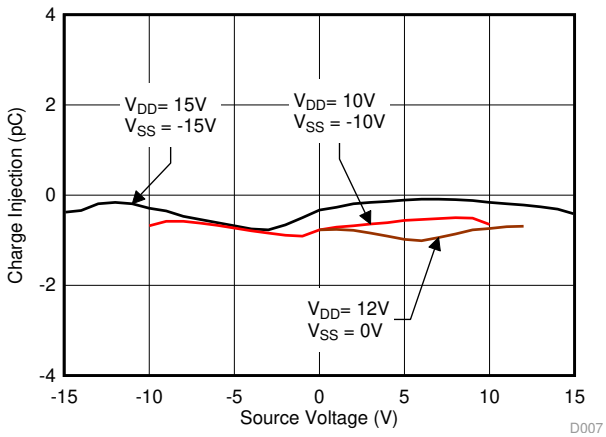


图 29. Source-to-Drain Charge Injection vs Source or Drain Voltage

9.3.3 Bidirectional and Rail-to-Rail Operation

The TMUX6111, TMUX6112, and TMUX6113 conduct equally well from source (Sx) to drain (Dx) or from drain (Dx) to source (Sx). Each channel of the switches has very similar characteristics in both directions. The input signal to the devices swings from V_{SS} to V_{DD} without any significant degradation in performance. The on-resistance of these devices varies with input signal.

9.4 Device Functional Modes

Each channel of the TMUX6111, TMUX6112, and TMUX6113 is turned on or turned off based on the state of its corresponding SELx pin. The SELx pins are weakly pulled-down through an internal 6 MΩ resistor, allowing the switches to stay in a determined state when power is applies to the devices. The SELx pins can be connected to V_{DD}.

10 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

10.1 Application Information

The TMUX6111, TMUX6112, and TMUX6113 offer outstanding input/output leakage currents and ultralow charge injection. These devices operate up to 34 (dual supply) or 17 V (single supply), and offer true rail-to-rail input and output. The on-capacitance of the TMUX6111, TMUX6112, and TMUX6113 is low. These features makes the TMUX6111, TMUX6112, and TMUX6113 a family of precision, robust, high-performance analog multiplexer for high-voltage, industrial applications.

10.2 Typical Application

One useful application to take advantage of TMUX6111, TMUX6112, and TMUX6113's precision performance is the sample and hold circuit. A sample and hold circuit can be useful for an analog to digital converter (ADC) to sample a varying input voltage with improved reliability and stability. It can also be used to store the output samples from a single digital-to-analog converter (DAC) in a multi-output application. A simple sample and hold circuit can be realized using an analog switch like one of the TMUX6111, TMUX6112, and TMUX6113 analog switches.

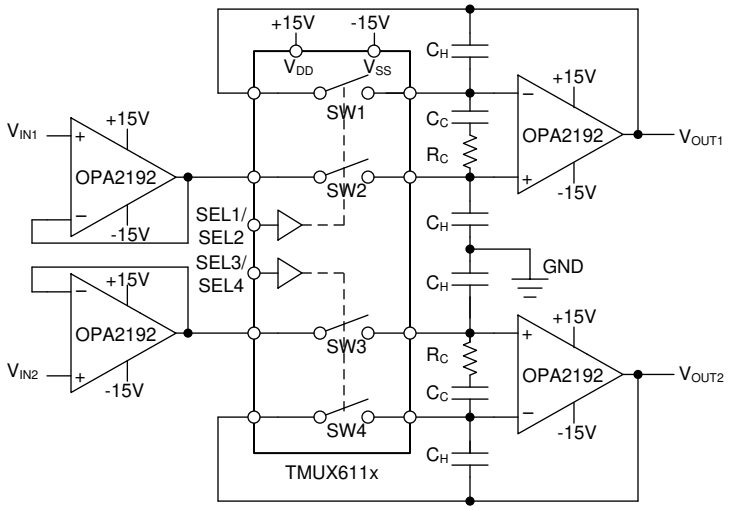


图 30. A 2-output Sample and Hold Circuit Realized Using the TMUX611x Analog Switch

Typical Application (接下页)

10.2.1 Design Requirements

The purpose of this precision design is to implement an optimized 2-output sample and hold circuit using a 4-channel SPST switch. The sample and hold circuit needs to be capable of supporting high voltage output swing up to ± 15V with minimized pedestal error and fast settling time. The overall system block diagram is illustrated in 图 30.

10.2.2 Detailed Design Procedure

The TMUX6111, TMUX6112, or TMUX6113 switch is used in conjunction with the voltage holding capacitors (C_H) to implement the sample and hold circuit. The basic operation is:

1. When the switch (SW2 or SW3) is closed, it samples the input voltage and charges the holding capacitors (C_H) to the input voltages values.
2. When the switch (SW2 or SW3) is open, the holding capacitors (C_H) holds its previous value, maintaining stable voltage at the amplifier output (V_{OUT}).

Ideally, the switch delivers only the input signals to the holding capacitors. However, when the switch gets toggled, some amount of charge also gets transferred to the switch output in the form of charge injection, resulting slight sampling error. The TMUX6111, TMUX6112, and TMUX6113 switches have excellent charge injection performance of only 0.6 pC, making them ideal choices for this implementation to minimize sampling error.

Due to switch and capacitor leakage current, the voltage on the hold capacitors droops with time. The TMUX6111, TMUX6112, and TMUX6113 minimize the droops due to its ultra-low leakage performance. At 25°C, the TMUX6111, TMUX6112, and TMUX6113 have extremely tiny leakage current at 1 pA typical and 20 pA max.

The TMUX6111, TMUX6112, and TMUX6113 devices also support high voltage capability. The devices support up to ± 17 V dual supply operation, making it an ideal solution in this high voltage sample and hold application.

A second switch SW1 (or SW4) is also included to operate in parallel with SW2 (or SW3) to reduce pedestal error during switch toggling. Because both switches are driven at the same potential, they act as common-mode signal to the op-amp, thereby minimizing the charge injection effects caused by the switch toggling action. Compensation network consisting of R_C and C_C is also added to further reduce the pedestal error, whiling reducing the hold-time glitch and improving the settling time of the circuit.

10.3 Application Curves

TMUX6111, TMUX6112, and TMUX6113 have excellent charge injection performance of only 0.6 pC (typical), making them ideal choices to minimize sampling error for the sample and hold application. 图 31 shows the plot for the charge injection vs. source input voltage for TMUX6111, TMUX6112, and TMUX6113.

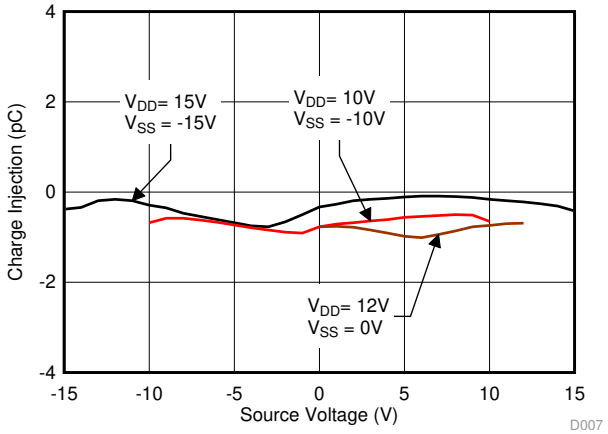


图 31. Charge injection vs. Source Voltage for TMUX6111, TMUX6112 and TMUX6113

11 Power Supply Recommendations

The TMUX6111, TMUX6112, and TMUX6113 operate across a wide supply range of ±5 V to ±17 V (10 V to 17 V in single-supply mode). They also perform well with asymmetrical supplies such as V_{DD} = 12 V and V_{SS}= –5 V. For improved supply noise immunity, use a supply decoupling capacitor ranging from 0.1 µF to 10 µF at both the V_{DD} and V_{SS} pins to ground. Always ensure the ground (GND) connection is established before supplies are ramped. As a best practice, it is recommended to ramp V_{SS} first before V_{DD} in dual or asymmetrical supply applications.

The on-resistance of the devices varies with supply voltage, as illustrated in 图 32

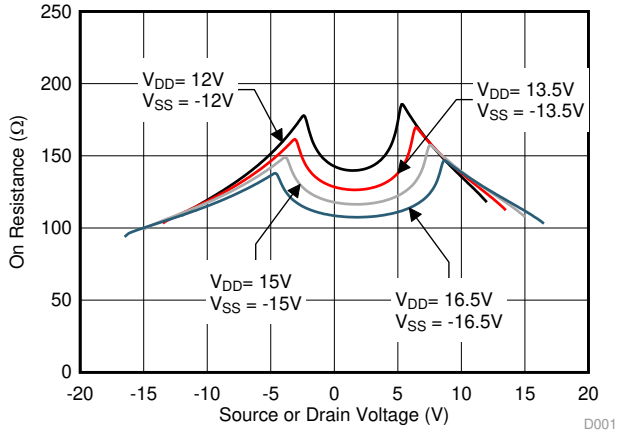


图 32. On-Resistance Variation With Supply and Input Voltage

12 Layout

12.1 Layout Guidelines

图 33 illustrates an example of a PCB layout with the TMUX6112PW. Some key considerations are:

- Decouple the V_{DD} and V_{SS} pins with a 0.1-µF capacitor, placed as close to the pin as possible. Make sure that the capacitor voltage rating is sufficient for the V_{DD} and V_{SS} supplies.
- Keep the input lines as short as possible.
- Use a solid ground plane to help distribute heat and reduce electromagnetic interference (EMI) noise pickup.
- Do not run sensitive analog traces in parallel with digital traces. Avoid crossing digital and analog traces if possible, and only make perpendicular crossings when necessary.

12.2 Layout Example

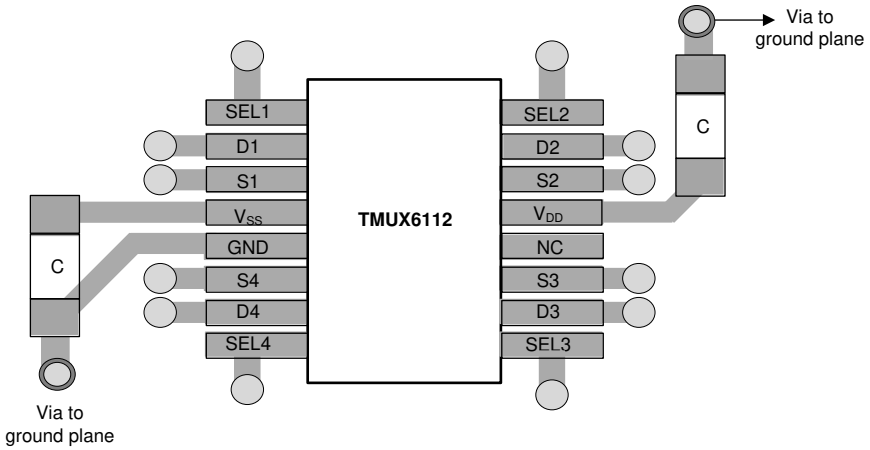


图 33. TMUX6112PW Layout Example

13 器件和文档支持

13.1 文档支持

13.1.1 相关文档

- *《采用 e-trim™ 技术的 OPAx192 36V、精密、轨到轨输入/输出、低偏移电压、低输入偏置电流运算放大器》* (SBOS620E)

13.2 相关链接

下表列出了快速访问链接。类别包括技术文档、支持和社区资源、工具和软件，以及立即订购快速访问。

表 **4.** 相关链接

器件	产品文件夹	立即订购	技术文档	工具与软件	支持和社区
TMUX6111	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
TMUX6112	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处
TMUX6113	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处

13.3 接收文档更新通知

要接收文档更新通知，请导航至 ti.com. 上的器件产品文件夹。单击右上角的*通知我*进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

13.4 支持资源

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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13.5 商标

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13.6 静电放电警告

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。 精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

13.7 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

14 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TMUX6111PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	MUX6111	Samples
TMUX6111RTER	ACTIVE	WQFN	RTE	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TM6111	Samples
TMUX6112PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	MUX6112	Samples
TMUX6112RTER	ACTIVE	WQFN	RTE	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TM6112	Samples
TMUX6113PWR	ACTIVE	TSSOP	PW	16	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	MUX6113	Samples
TMUX6113RTER	ACTIVE	WQFN	RTE	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	TM6113	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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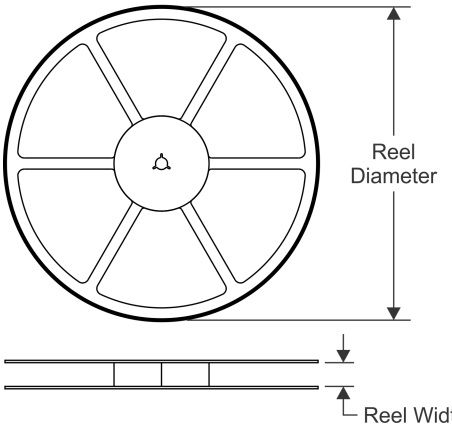
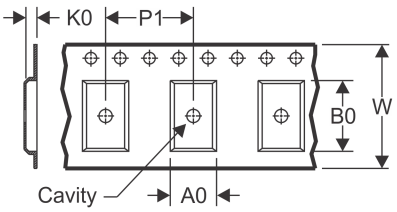
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

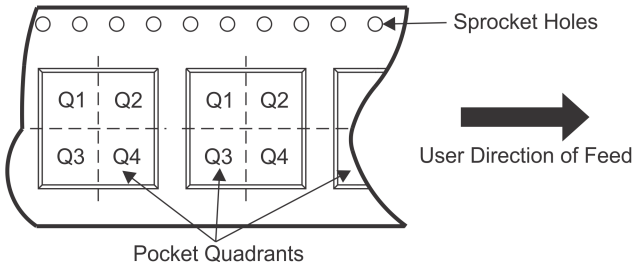


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

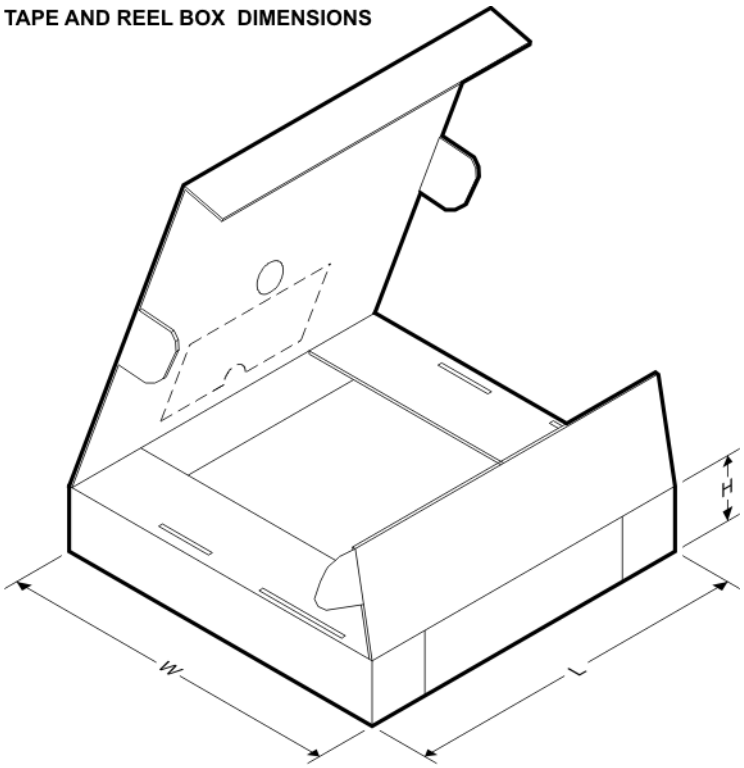
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TMUX6111PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TMUX6111RTER	WQFN	RTE	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TMUX6112PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TMUX6112RTER	WQFN	RTE	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TMUX6113PWR	TSSOP	PW	16	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
TMUX6113RTER	WQFN	RTE	16	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

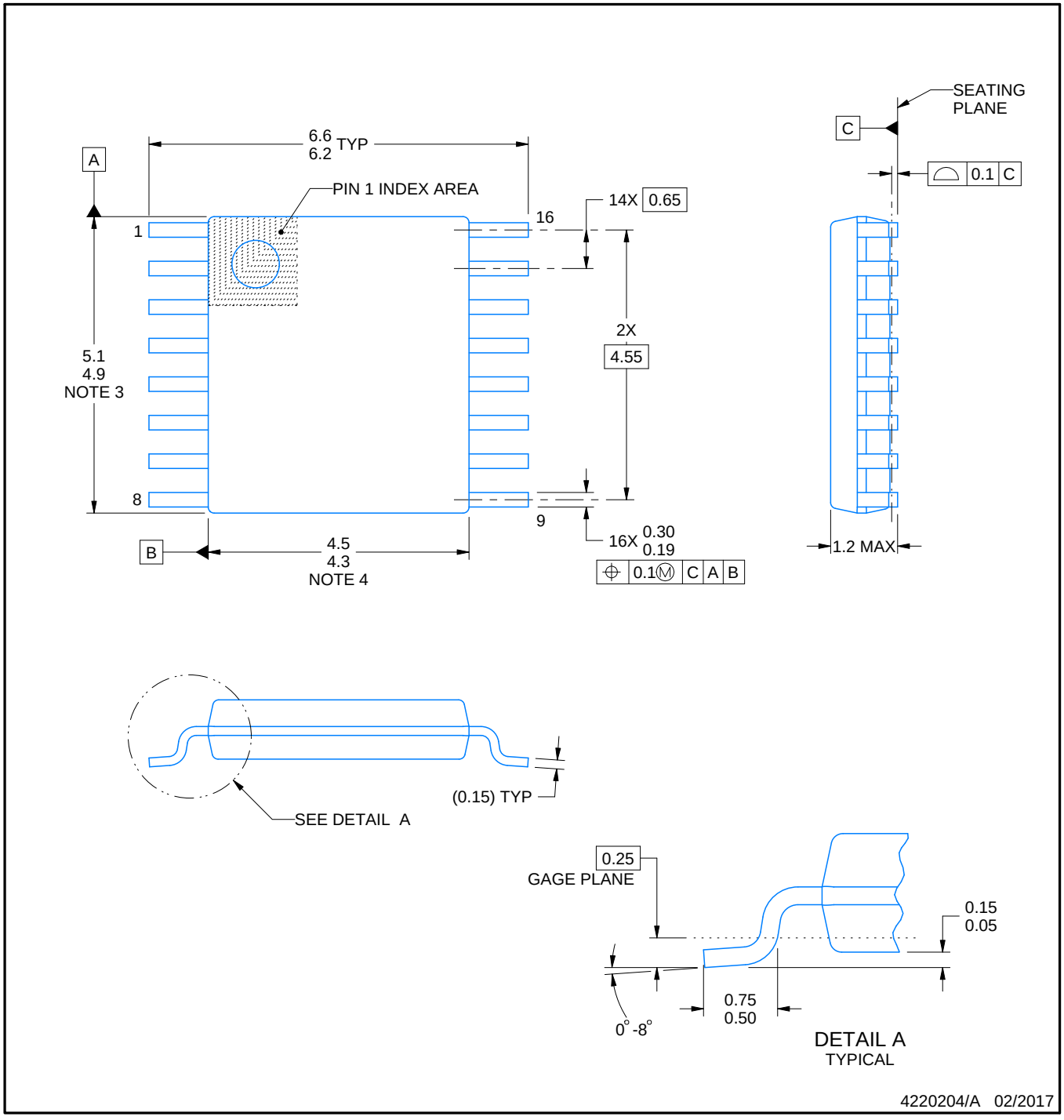
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TMUX6111PWR	TSSOP	PW	16	2000	853.0	449.0	35.0
TMUX6111RTER	WQFN	RTE	16	3000	367.0	367.0	35.0
TMUX6112PWR	TSSOP	PW	16	2000	853.0	449.0	35.0
TMUX6112RTER	WQFN	RTE	16	3000	367.0	367.0	35.0
TMUX6113PWR	TSSOP	PW	16	2000	367.0	367.0	35.0
TMUX6113RTER	WQFN	RTE	16	3000	367.0	367.0	35.0

PACKAGE OUTLINE

PW0016A

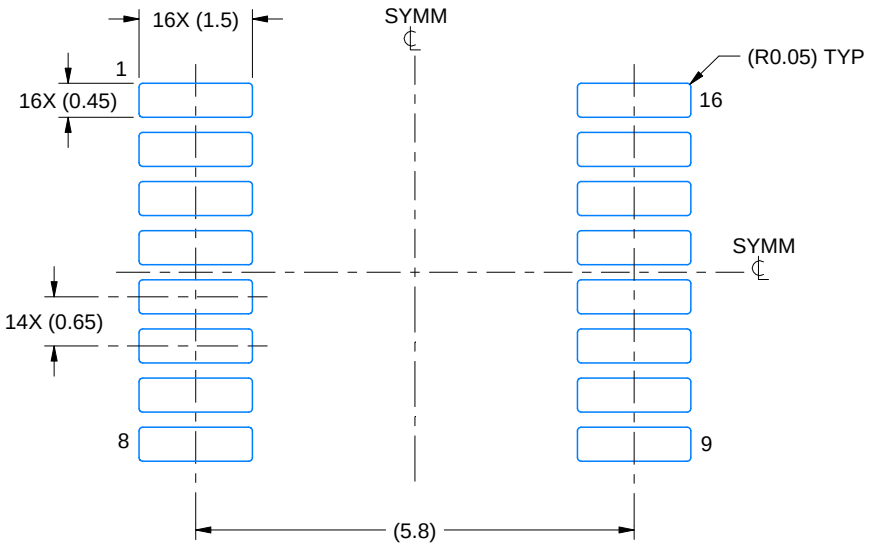
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

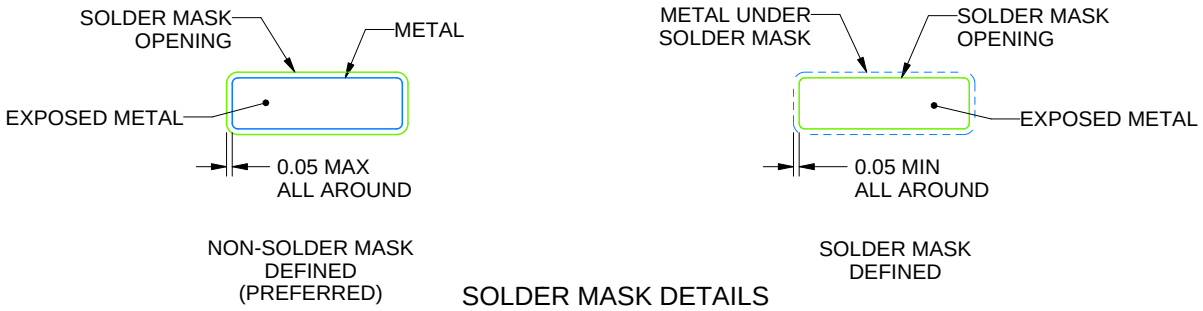


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

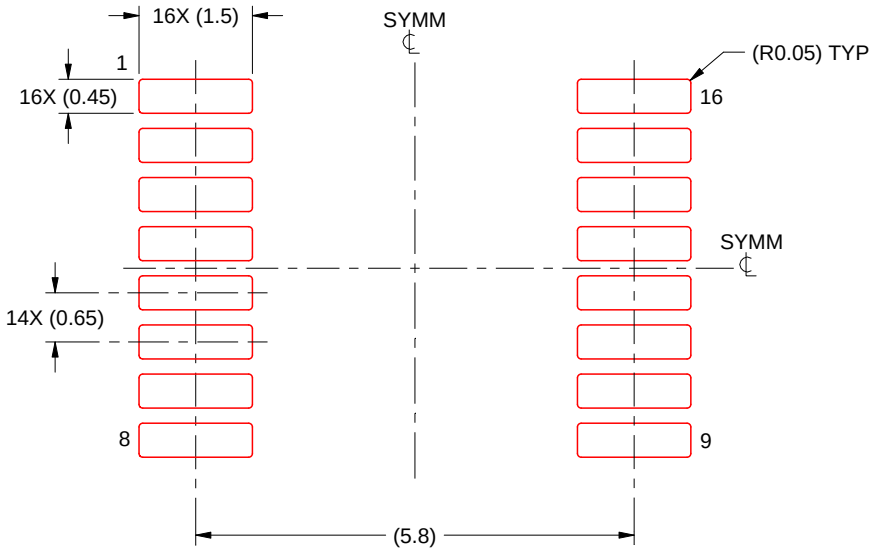


SOLDER MASK DETAILS

4220204/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

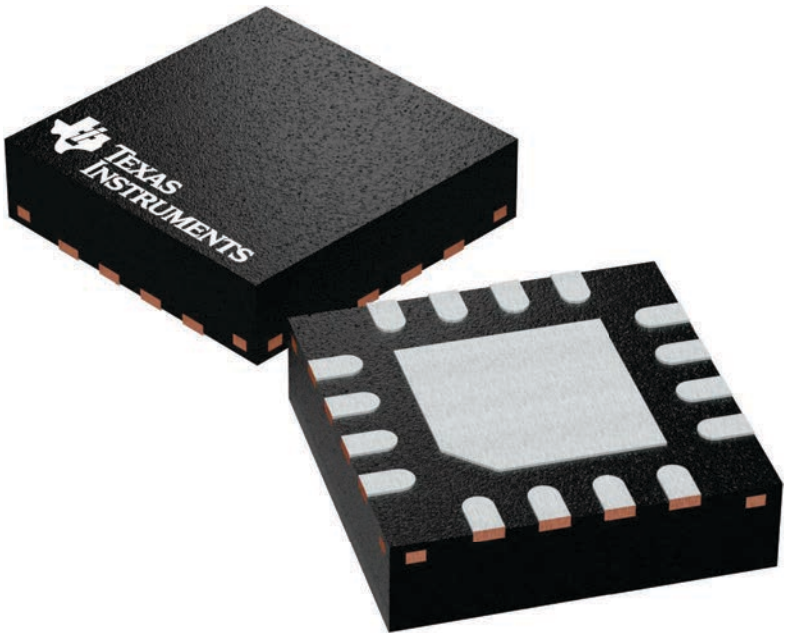
RTE 16

WQFN - 0.8 mm max height

3 x 3, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

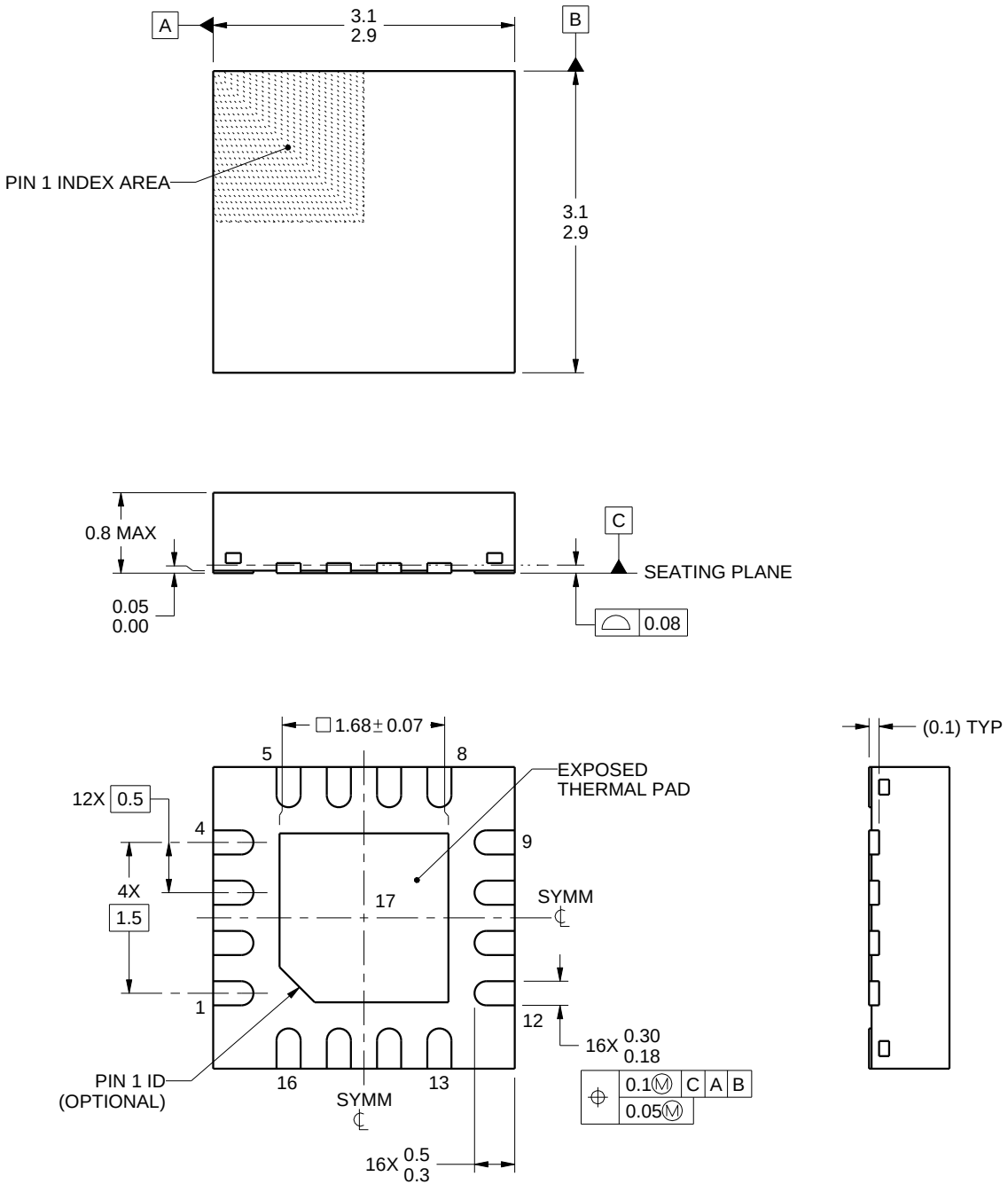


PACKAGE OUTLINE

RTE0016C

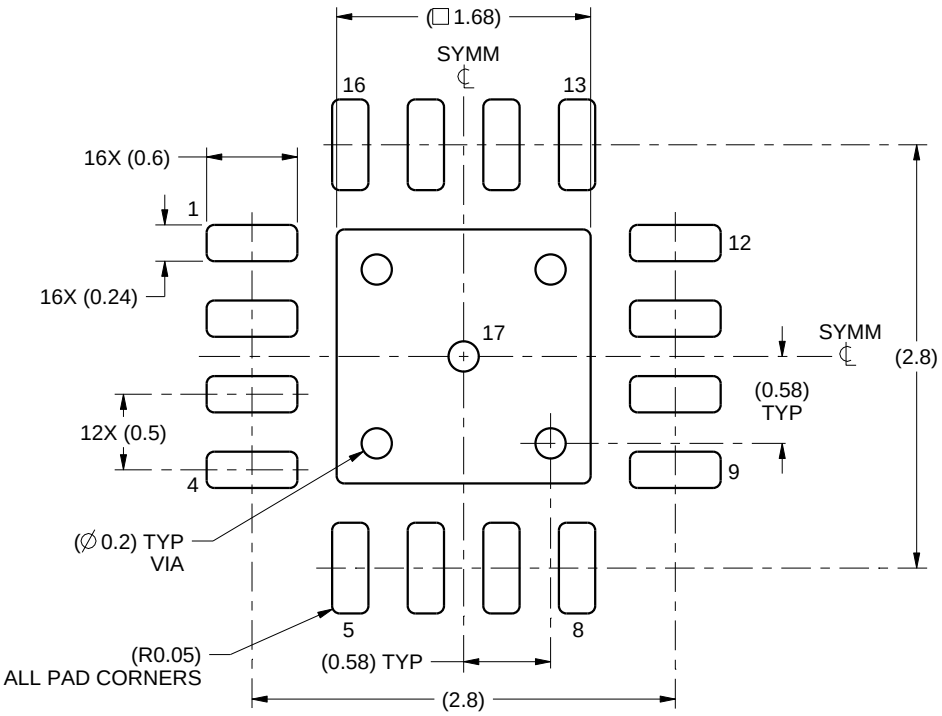
WQFN - 0.8 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

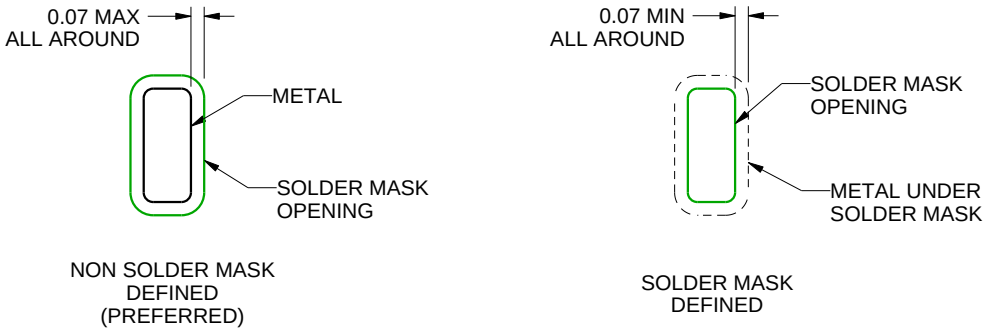


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE
SCALE:20X

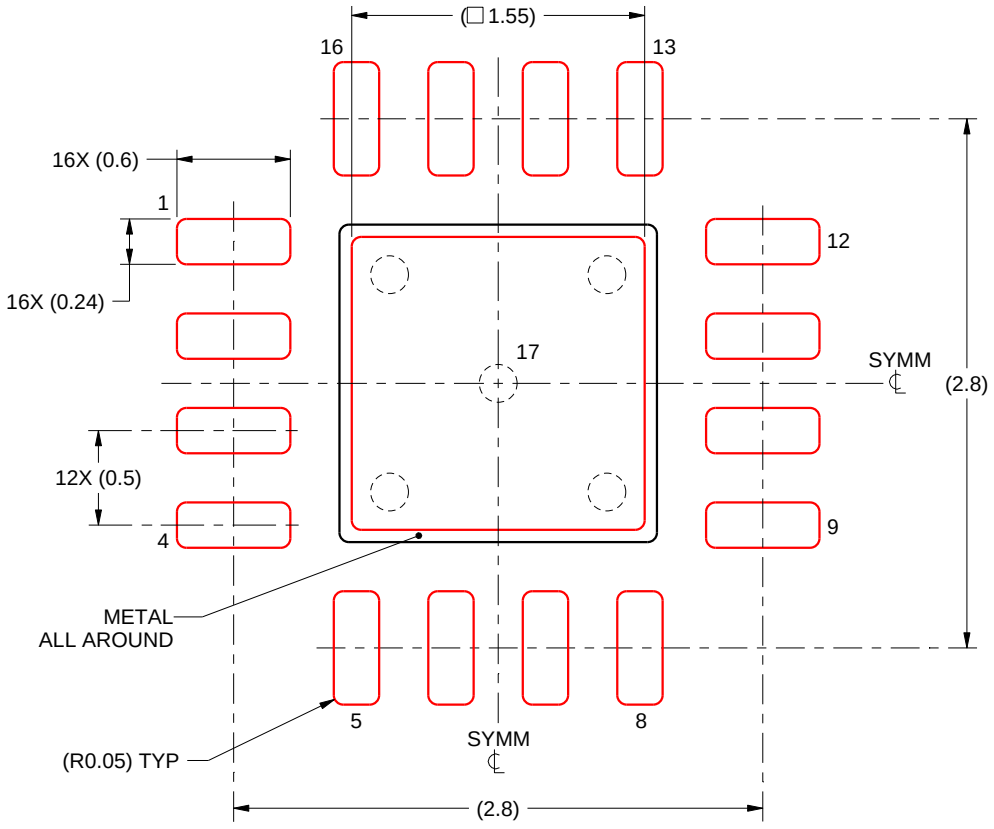


SOLDER MASK DETAILS

4219117/A 09/2016

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 17:
85% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:25X

4219117/A 09/2016

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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